

<b>SANYO</b>	No.5313A	<b>2SJ419</b> P-Channel MOS Silicon FET
<b>Ultrahigh-Speed Switching Applications</b>		

**Features**

- Low ON-resistance.
- Ultrahigh-speed switching.
- 2.5V drive.

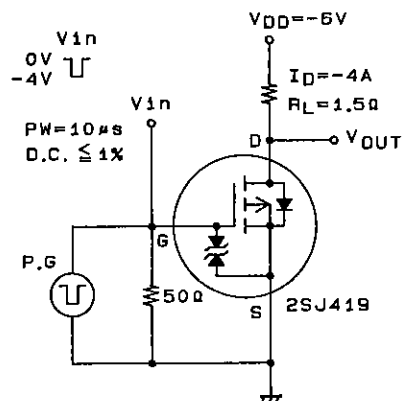
**Absolute Maximum Ratings at Ta = 25°C**

			unit
Drain-to-Source Voltage	V <sub>DSS</sub>	-12	V
Gate-to-Source Voltage	V <sub>GSS</sub>	±10	V
Drain Current (DC)	I <sub>D</sub>	-4	A
Drain Current (Pulse)	I <sub>DP</sub>	-32	A
Allowable Power Dissipation	P <sub>D</sub>	2.0	W
		Mounted on ceramic board (1200mm <sup>2</sup> × 0.8mm)	
Channel Temperature	T <sub>ch</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

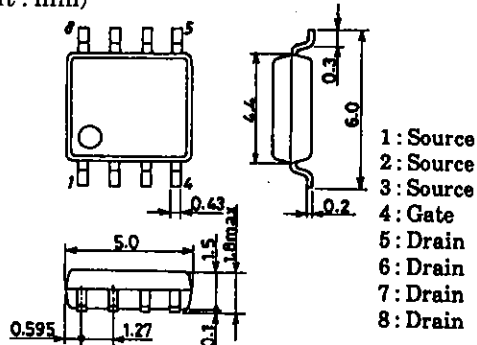
**Electrical Characteristics at Ta = 25°C**

			min	typ	max	unit
D-S Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = -1mA, V <sub>GS</sub> = 0	-12			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -10V, V <sub>GS</sub> = 0			-100	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±8V, V <sub>DS</sub> = 0			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> = -6V, I <sub>D</sub> = -1mA	-0.4		-1.4	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> = -6V, I <sub>D</sub> = -4A	6	8		S
Static Drain-to-Source ON-State Resistance	R <sub>DS(on)1</sub>	I <sub>D</sub> = -4A, V <sub>GS</sub> = -4V		65	82	mΩ
ON-State Resistance	R <sub>DS(on)2</sub>	I <sub>D</sub> = -2A, V <sub>GS</sub> = -2.5V		90	144	mΩ
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -6V, f = 1MHz		1000		pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> = -6V, f = 1MHz		800		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	V <sub>DS</sub> = -6V, f = 1MHz		420		pF
Turn-ON Delay Time	t <sub>d(on)</sub>	See specified Test Circuit.		25		ns
Rise Time	t <sub>r</sub>	"		170		ns
Turn-OFF Delay Time	t <sub>d(off)</sub>	"		180		ns
Fall Time	t <sub>f</sub>	"		270		ns
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = -4A, V <sub>GS</sub> = 0	-1.0	-1.2		V

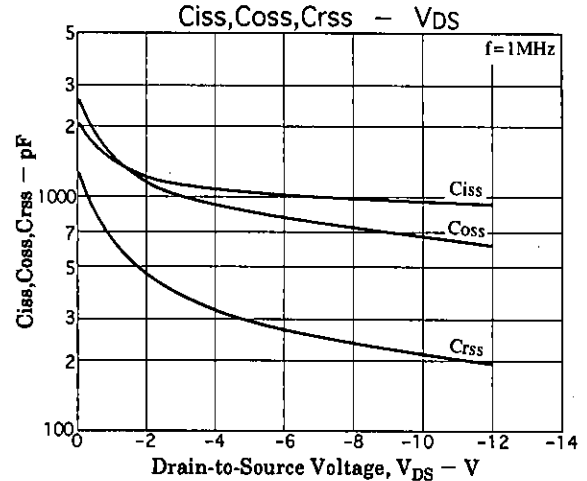
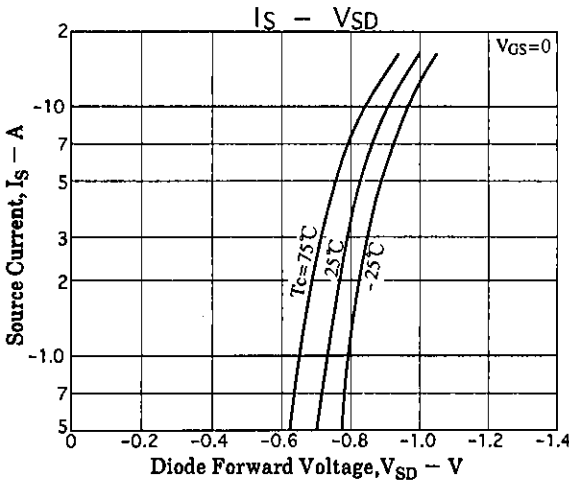
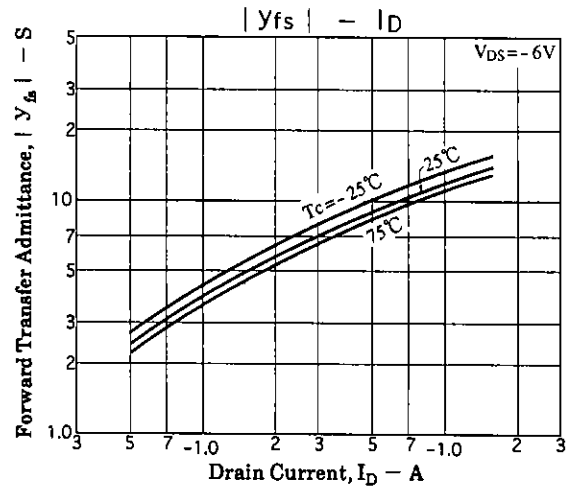
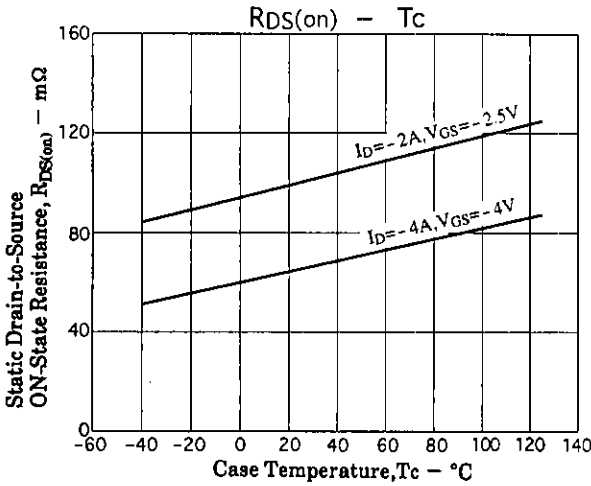
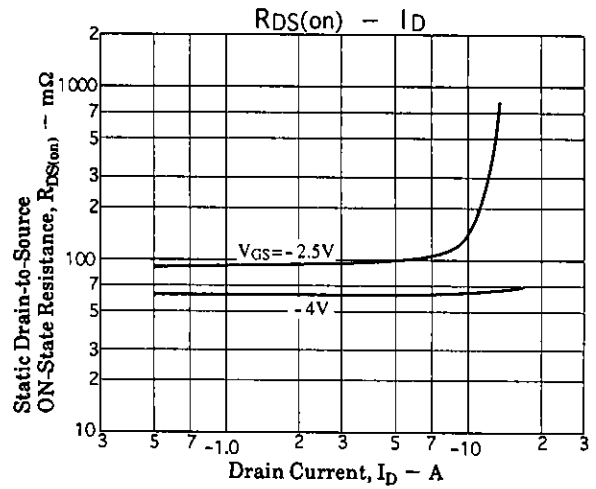
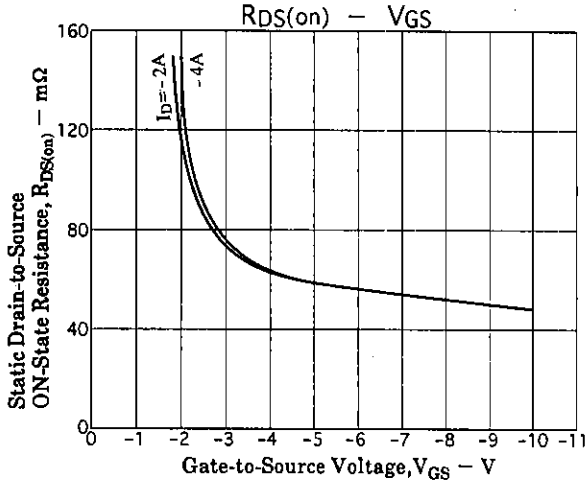
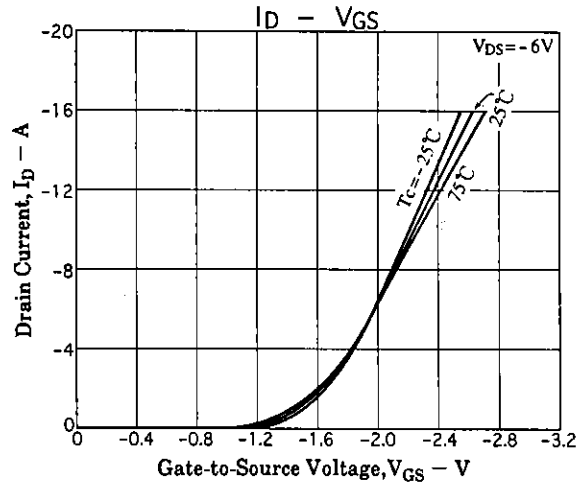
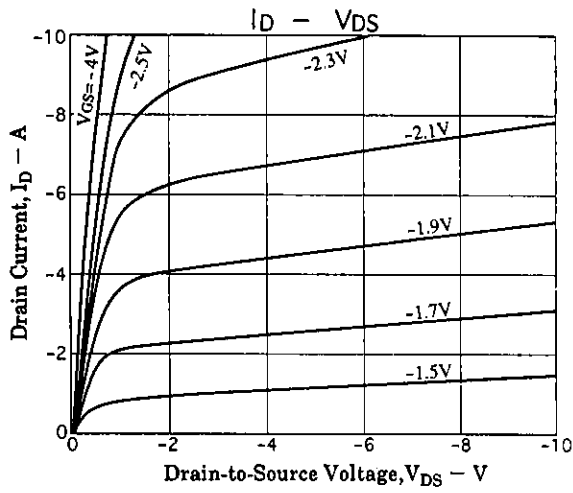
**Switching Time Test Circuit**

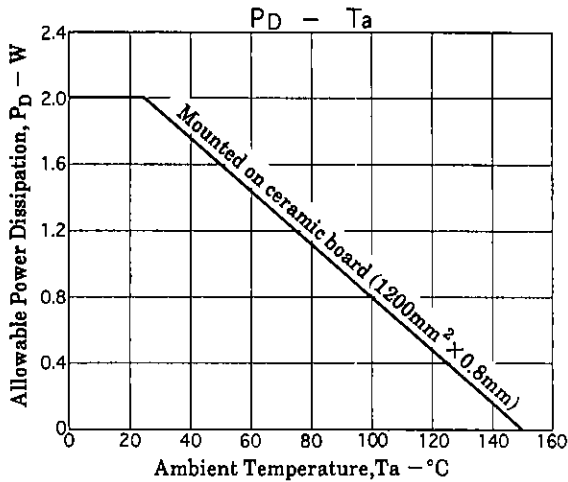
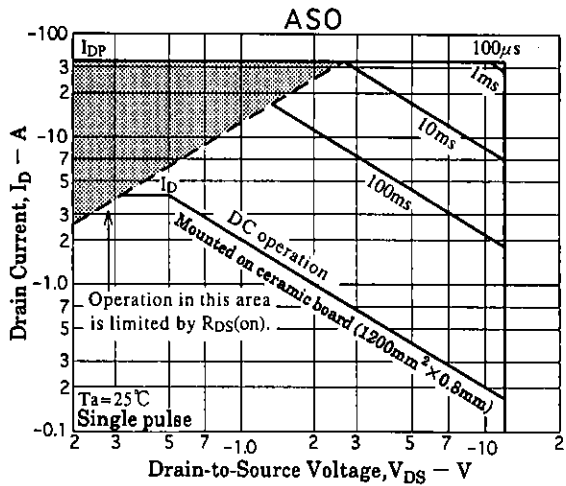
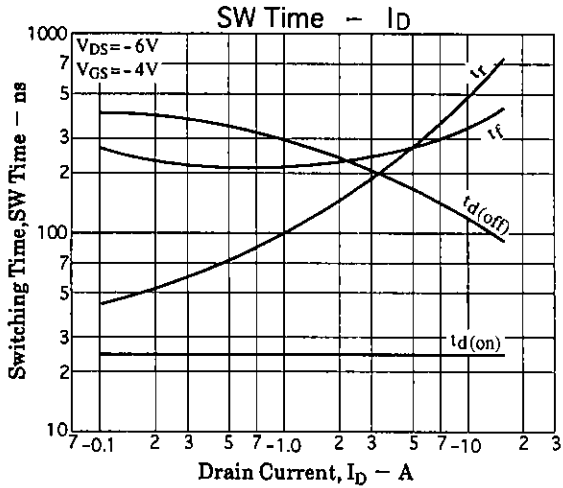


**Package Dimensions 2116**  
(unit: mm)



SANYO: SOP8





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